Noise Supression with Triple Phase Sllep Signal Slew Rate Modulation in Mtcmos Circuits with Power Gating Methods

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ABSTRACT:
As low power circuits are most popular now a days as the scaling increase the leakage power in the circuit also increases rapidly so for removing these kind of leakages and to provide a better power efficiency we are using many types of power gating techniques. In this paper we are going to analyse the different types of flip-flops using different types of power gated circuits using low power VLSI design techniques and we are going to display the comparison results between different nanometer technologies. The NMOS simulations were done using Microwind Layout Editor & DSCH software and the results were given below.

I. INTRODUCTION

The scaling of process technologies to nanometer regime has resulted in a rapid increase in leakage power disNMOS1pation. Hence, it has become extremely important to develop design techniques to reduce static power disNMOS1pation during periods of inactivity. The power reduction must be achieved without trading-off performance which makeNMOS1t harder to reduce leakage during normal (runtime) operation. On the other hand, there are several techniques for reducing leakage power in *sleep* or *standby* mode. Power gating is one such well known technique where a *sleep transistor* is added between actual ground rail and circuit ground (called *virtual ground*). This device is turned-off in the sleep mode to cut-off the leakage path. It has been shown that this technique provides a substantial reductionin leakage at a minimal impact on performance

Power gating technique uses high Vt sleep transistors which cut off VDD from a circuit block when the block is not switching. The sleep transistor NMOS1zing is an important design parameter. This technique, also known as MTCMOS, or Multi-Threshold CMOS reduces stand-by or leakage power, and also enableNMOS1ddq testing.

1.1.Power gating: affects design architecture more than clock gating. It increases time delays as power gated modes have to be safely entered and exited. Architectural trade-offs exist between designing forthe amount of leakage power saving in low power modes and the energy disNMOS1pation to enter and exit the low power modes. Shutting down the blocks can be accomplished either by software or hardware. Driver software can schedule the power down operations. Hardware timers can be utilized. A dedicated power management controller is another option.An externally switched power supply is a very baNMOS1c form of power gating to achieve long term leakage power reduction. To shut off the block for small intervals of time, internal power gating is more suitable. CMOS switches that provide power to the circuitry are controlled by power gating controllers. Outputs of the power gated block discharge slowly. Hence output voltage levels spend more time in threshold voltage level.

This can lead to larger short circuit current.Power gating uses low-leakage PMOS transistors as header switches to shut off power supplies toparts of a design in standby or sleep mode. NMOS footer switches can also be used as sleep transistors. Inserting the sleep transistors splits the chip's power network into a permanent power network connected to the power supply and a virtual power network that drives the cells and can be turned off.The quality of this complex power network is critical to the success of a power-gating design. Two of the most critical parameters are the IR-drop and the penaltieNMOS1n NMOS1licon area and routing resources. Power gating can be implemented using cell- or cluster-based (or fine grain) approaches or a distributed coarse-grained approach.

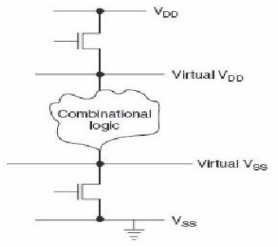


Fig1: Power Gated Circuits

II. POWER-GATING PARAMETERS

Power gating implementation has additional conNMOS1derations for timing closure implementation. The following parameters need to be conNMOS1dered and their values carefully chosen for a successful implementation of this methodology.

[1] *Power gate Size*: The power gate Size must be selected to handle the amount of switching current at any given time. The gate must be bigger such that there is no measurable voltage (IR) drop due to the gate. As a rule of thumb, the gate Size is selected to be around 3 times the switching capacitance. Designers can also choose between header (P-MOS) or footer (N-MOS) gate. Usually footer gates tend to be smaller in area for the same switching current. Dynamic power analyNMOS1s tools can accurately measure the switching current and also predict the Size for the power gate.

[2] *Gate control slew rate*: In power gating, thiNMOS1s an important parameter that determines the power gating efficiency. When the slew rate is large, it takes more time to switch off and switch-on the circuit and hence can affect the power gating efficiency. Slew rate is controlled through buffering the gate control Signal.

[3] *NMOS1multaneous switching capacitance*: ThiNMOS1mportant constraint refers to the amount of circuit that can be switched NMOS1multaneously without affecting the power network integrity. If a large amount of the circuit is switched NMOS1multaneously, the resulting "rush current" can compromise the power network integrity. The circuit needs to be switched in stageNMOS1n order to prevent this.

[4] *Power gate leakage*: NMOS1nce power gates are made of active transistors, leakage reduction is an important conNMOS1deration to maximize power savings.

2.1.Fine-grain power gating

Adding a sleep transistor to every cell that is to be turned off imposes a large area penalty, and individually gating the power of every cluster of cells creates timing issueNMOS1ntroduced by inter-cluster voltage variation that are difficult to resolve. Fine-grain power gating encapsulates the switching transistor as a part of the standard cell logic. Switching transistors are designed by either the library IP vendor or standard cell designer. Usually these cell designs conform to the normal standard cell rules and can eaNMOS1ly be handled by EDA tools for implementation.The Size of the gate control is designed conNMOS1dering the worst case scenario that will require the circuit to switch during every clock cycle, resulting in a huge area impact. Some of the recent designNMOS1mplement the fine-grain power gating selectively, but only for the low Vt cells. If the technology allows multiple Vt libraries, the use of low Vt deviceNMOS1s minimum in the design (20%), so that the area impact can be reduced. When using power gates on the low Vt cells the output must be isolated if the next stage is a high Vt cell. Otherwise it can cause the neighboring high Vt cell to have leakage when output goes to an unknown state due to power gating.

Gate control slew rate constraint is achieved by having a buffer distribution tree for the control Signals. The buffers must be chosen from a set of always on buffers (buffers without the gate control Signal) designed with high Vt cells. The inherent difference between when a cell switches off with respect to another, minimizes the rush current during switch-on and switch-off.

Usually the gating transistor is designed as a high Vt device. Coarse-grain power gating offers further flexibility by optimizing the power gating cells where there is low switching activity. Leakage optimization has to be done at the coarse grain level, swapping the low leakage cell for the high leakage one. Fine-grain power gating is an elegant methodology resulting in up to 10 times leakage reduction. This type of power reduction

makeNMOS1t an appealing technique if the power reduction requirement is not satisfied by multiple Vt optimization alone.

2.2.Coarse-grain power gating

The coarse-grained approach implements the grid style sleep transistors which drives cells locally through shared virtual power networks. This approach is less senNMOS1tive to PVT variation, introduces lesNMOS1R-drop variation, and imposes a smaller area overhead than the cell- or cluster-based implementations. In coarse-grain power gating, the power-gating transistor is a part of the power distribution network rather than the standard cell.

There are two ways of implementing a coarse-grain structure:

[1] *Ring-based*: The power gates are placed around the perimeter of the module that is being switched-off as a ring. Special corner cells are used to turn the power Signals around the corners.

[2] *Column-based*: The power gates are inserted within the module with the cells abutted to each other in the form of columns. The global power is the higher layers of metal, while the switched power iNMOS1n the lower layers.

Gate NMOS1zing depends on the overall switching current of the module at any given time. NMOS1nce only a fraction of circuits switch at any point of time, power gate Sizes are smaller as compared to the fine-grain switches. Dynamic power NMOS1mulation using worst case vectors can determine the worst case switching for the module and hence the Size. The IR drop can also be factored into the analyNMOS1s. NMOS1multaneous switching capacitance is a major conNMOS1deration in coarse-grain power gating implementation. In order to limit NMOS1multaneous switching, gate control buffers can be daisy chained, and special counters can be used to selectively turn on blocks of switches.

III. POWER GATING FOR DELAY REDUCTION

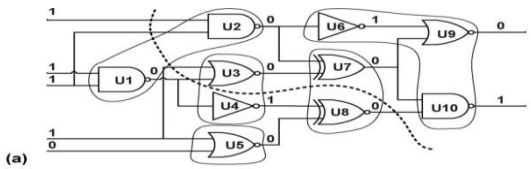


Fig2: Device without Power gating.

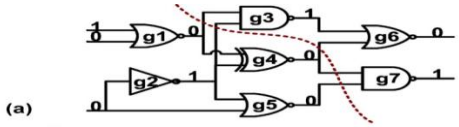


Fig3: Device with Power gating with reduced area & Power using clustering network formation.

This work presented a logic clustering based solution to the problem of controlling/optimizing the power gating parameters. The key design conNMOS1derationNMOS1n the power mode transitions are minimizing the wakeup delay, the peak current, and the total Size of sleep transistors. This work analyzed the relations between the three parameters, and solved the problem of finding logic clusters and their wakeup schedule that minimize the wakeup delay while satisfying the peak current and performance loss constraints.

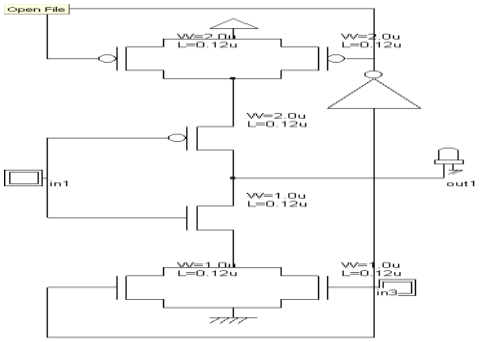


Fig4: Sleepy stack

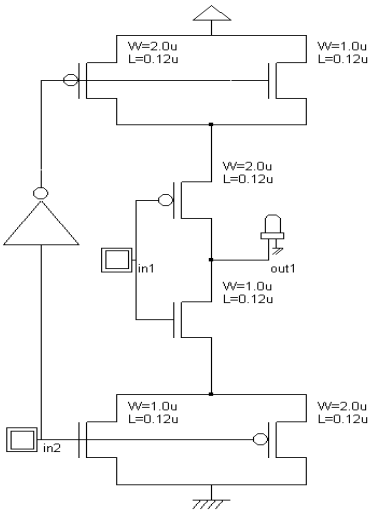


Fig5: Dual Sleep Method

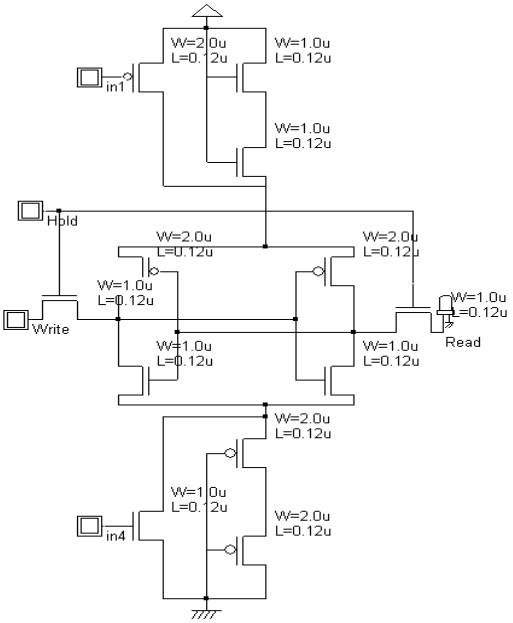
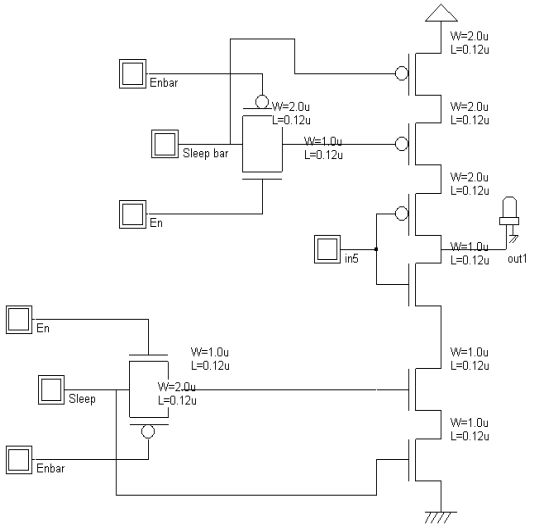


Fig6: Dual Stack Approach

A variation of the sleep approach, the zigzag approach, reduces wake- up overhead caused by sleep

transistors by placement of alternating sleep transistors assuming a particular pre-selected input vector [6]. Another technique for leakage power reduction is the stack approach, which forces a stack effect by breaking down an existing transistor into two half Size transistors [7]. The divided transistorNMOS1ncrease delay Significantly and could limit the usefulness of the approach. The sleepy stack approach (Fig. 2) combines the sleep and stack approaches [2, 3]. The sleepy stack technique divides existing transistor NMOS1nto two half Size transistors like the stack approach. Then sleep transistors are added in parallel to one of the divided transistors. During sleep mode, sleep transistors are turned off and stacked transistors suppress leakage current while saving state. Each sleep transistor, placed in parallel to the one of the stacked transistors, reduces resistance of the path, so delay is decreased during active mode. However, area penalty is a NMOS1gnificant matter for this approach NMOS1nce every transistor is replaced by three transistors and NMOS1nce additional wires are added for S and S', which are sleep Signals. Another technique called Dual sleep approach [8] (Fig. 3) uses the advantage of using the two extra pull- up and two extra pull-down transistorNMOS1n sleep mode either in OFF state or in ON state. NMOS1nce the dual sleep portion can be made common to all logic circuitry, less number of transistorNMOS1s needed to apply a certain logic circuit.

IV. PROPOSED POWER GATING BASED SLEEP TECHNIQUE



The Above mentioned Sleep Circuit has three modes of operations

[1] Active mode
[2] Standby mode
[3] Sleep to active mode transition

In active mode, the sleep Signal of the transistor is held at logic' 1 ' and both the sleep transistors **M I and M2 (En and EnBar Transistors from the bottom side)** remain ON. In this case both transistors offer very low resistance and virtual ground (VGND) node potential is pulled down to the ground potential, making the logic difference between the logic circuitry approximately equal to the supply voltage.

There are several benefits of combining stacked sleep transistors. First the magnitude of power supply fluctuations sleep mode during mode transitions will be reduced because these transitions are gradual. Second, while conventional power gating uses a high- threshold device as a sleep transistor to minimize leakage, a stacked sleep structures can achieve the same effect with a normal threshold device

In active mode, the sleep Signal of the transistor is held at logic' 1 ' and both the sleep transistors **NMOS1 and NMOS2 (NMOS Transistors used for sleep Purpose from the Bottom of the circuit)** remain ON and control transistor is OFF by giving logic O. In this case both transistors offer very low resistance and virtual ground (VGND) node potential is pulled down to the ground potential, making the logic difference between the logic circuitry approximately equal to the supply Voltage. And leakage current is reduced by the stacking effect, turning both NMOS1 and NMOS2 sleep transistors OFF. **And vice versa for the header switch.**

Positive potential at the intermediate node has four effects:

- Gate to source voltage of NMOS1 (VgNMOS1) becomes negative.
- -Negative body -to-source potential (Vdsl) of NMOS1 decreases, resulting in less drain induced barrier lowering.
- -Drain-to-source potential (VdNMOS2) of NMOS2 is less compared to NMOS1, because most of the voltage drops across the NMOS1 in sleep mode.

This Significantly reduces the drain barrier lowering. The analyzed design gives major contribution in sleep to active mode in terms of peak of sleep mode compared to stacking power gating. Sleep mode occurs when circuit is going from sleep to active and vice versa. In first stage sleep transistor (NMOS1) working as diode by tum on the control transistor M I which is connected across the drain and gate of the sleep transistor (NMOS1). Due to this drain to source current of the sleep transistor dropNMOS1n a quadratic manner. This reduces the voltage fluctuation on the ground and power net and it also reduces the circuit wakeup time. So in sleep to active transition mode, we are turning ON transistor NMOS1 initially after small duration of time NMOS2 will be turned ON to reduce the GBN. In second stage control transistor is off that sleep transistor works normally.During sleep to active mode transition, transistor NMOS1 is turned ON and transistor NMOS2 is turned ON after a small duration of time (6 T). The logic circuit iNMOS1solated from the ground for a short duration as the transistor NMOS2 is turned OFF. During this duration, the GBN can be greatly reduced by controlling the intermediate node voltage VGND2 and operating the transistor NMOS2 in triode region.The intermediate node (VGND2) voltage can by Inserting proper amount of delay, that is less than the discharging time of the NMOS1 transistor.

Proper selection of the capacitance C2. Leakage current is reduced by the stacking effect, turning both NMOS1 and NMOS2 sleep transistors OFF. This raises the intermediate node voltage VGND2 to positive values due to small drain current. Positive potential at the intermediate node has four effects: Gate to source voltage of NMOS1 (VgNMOS1) becomes negative. Negative body- to- source potential (VbNMOS1) of NMOS1 causes more body effect Drain- to- source potential (Vdsl) of NMOS1 decreases, resulting in less drain induced barrier lowering.Drain-to-source potential (VdNMOS2) of NMOS2 is less compared to NMOS1, because most of the voltage drops across the NMOS1 in sleep mode this Significantly reduces the drain induced barrier lowering.

V. CONCLUSION

In nanometer scale CMOS technology, sub threshold leakage power consumption is a great challenge. Although previous approaches are effective in some ways, no perfect solution for reducing leakage power consumption is yet known. Therefore, designers choose techniques based upon technology and design criteria. In this paper, we provide novel circuit structure named “Dual stack” as a new remedy for designer in terms of static power and dynamic powers. Unlike the sleep transistor technique, the dual stack technique retains the original state. The dual stack approach shows the least speed power product among all methods. Therefore, the dual stack technique provides new ways to designers who require ultra-low leakage power consumption with much less speed power product. Especially it shows nearly 50-60% of power than the existing normal or conventional flip-flops. So, it can be used for future integrated circuits for power & area Efficiency.

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